

Listing of Claims and Amendments thereto:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Amended) A method of producing an acoustic resonator device, comprising:
 depositing a first metal film on a substrate;
 depositing piezoelectric material on said first metal film;
 depositing a second metal film on said piezoelectric material;
 patterning said second metal film; and
 isolating said piezoelectric material by selectively removing some or all piezoelectric material not involved in signal transmission to reduce an amount of acoustic energy which propagates in a lateral direction away from the device.
2. (Original) The method of claim 1, wherein said isolation of said piezoelectric material is performed during fabrication of the device.
3. (Original) The method of claim 1, wherein said isolation of said piezoelectric material is performed after fabrication of the device.
4. (Original) The method of claim 1, wherein said step of isolating further includes removing some or all piezoelectric material not involved in signal transmission after device fabrication to limit lateral propagation losses to un-etched regions of the device.
5. (Original) The method of claim 4, wherein said step of removing is performed by a selective etching process.

Claims 6-9 (Withdrawn)

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10. (Original) The method of claim 1, wherein said piezoelectric material is selected from the group comprising at least AlN, ZnO and CdS.

11. (Currently Amended) The method of claim 1, wherein said ~~conductive~~ first and second metal films are formed by lithographic patterning of Al metal or other conductors.

12. (Previously Amended) The method of claim 1, wherein said substrate is formed as a plurality of acoustic reflecting layers on a substrate such as a silicon, quartz, or glass wafer.

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13. (Previously Amended) A method of isolating an acoustic resonator device, comprising:
depositing a first metal film on a substrate;
patterning said first metal film;
depositing piezoelectric material on said first metal film;
depositing a second metal film on said piezoelectric material;
patterning said second metal film; and
removing some or all piezoelectric material not involved in signal transmission after device fabrication to limit lateral propagation losses to un-etched regions of the device, thereby limiting propagation of energy in lateral modes.

14. (Original) The method of claim 13, wherein said step or removing is performed by a elective etching process.

15. (Original) The method of claim 14, wherein at least some of the substrate surface is removed by selective etching.

16. (Original) The method of claim 13, wherein at least some of the removed piezoelectric material forms a void which is back filled with a different material.

Claims 17-28 (Withdrawn)